

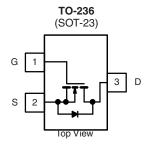
K4035-VB Datasheet N-Channel 200 V (D-S) MOSFET

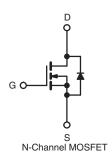
PRODUC	T SUMMARY	
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)
200	1.4 at V _{GS} = 10 V	0.6

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- 100 % $\rm R_{\rm g}$ and UIS Tested
- Trench Power MOSFET
- Compliant to RoHS Directive 2002/95/EC







Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	200		
Gate-Source Voltage		V _{GS}	± 20		V
Continuous Dunis Comment /T 150 °C\ ³	T _A = 25 °C		0.6	0.45	•
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	I _D	0.5	0.35	
Pulsed Drain Current ^b		I _{DM}		5	Α
Avalanche Current ^b	L = 0.1 mH	I _{AS}	2.5		
Single Avalanche Energy	L = 0.1 min	E _{AS}	5	0	mJ
Continuous Source Current (Diode Conduction) ^a		I _S	0.6		Α
Power Discinstian ^a	T _A = 25 °C	В	1.55	1.03	W
Power Dissipation ^a	T _A = 70 °C	P_{D}	1.20	0.87	VV
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 t	o 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 s	D	80	100	
Maximum sunction-to-Ambient	Steady State	R _{thJA}	130	170	°C/W
Maximum Junction-to-Foot	Steady State	R _{thJF}	45	55	

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.

服务热线:400-655-8788

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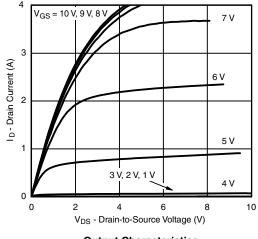
_		·		Limits		
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V _{GS} = 0 V, I _D = 1 mA	200			V
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.5		4.5	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zoro Cata Valtaga Drain Current		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$			1	
Zero Gate Voltage Drain Current	IDSS	V_{DS} = 100 V, V_{GS} = 0 V, T_{J} = 70 °C			75	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 15 \text{ V}, V_{GS} = 10 \text{ V}$	2.5			Α
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 A		1.4		Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 0.5 A		4		S
Diode Forward Voltage	V_{SD}	I _S = 1 A, V _{GS} = 0 V		0.8	1.2	V
Dynamic ^b						
Total Gate Charge	Q_g			3	5	
Gate-Source Charge	Q_{gs}	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$		0.37		nC
Gate-Drain Charge	Q _{gd}			1.45		
Gate Resistance	R_g		0.5	1.3	2.4	Ω
Switching						
Turn-On Delay Time	t _{d(on)}			7	11	
Rise Time	t _r	V_{DD} = 100 V, R_L = 33 Ω		10	15	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 0.2$ A, V_{GEN} = 10 V, R_g = 6 Ω		9	15	ns
Fall Time	t _f			11	15	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 0.5 A, dl/dt = 100 A/μs50100				

Notes:

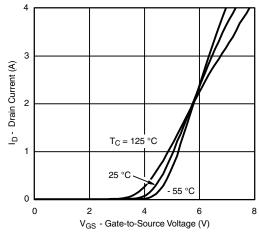
- a. Pulse test: PW \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



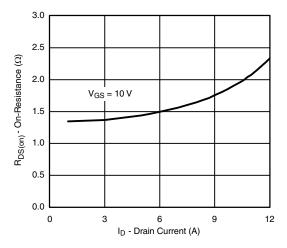




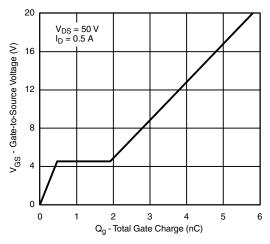
Transfer Characteristics



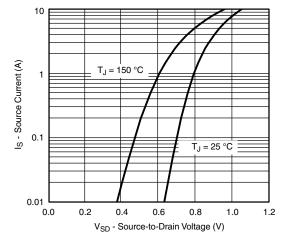
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



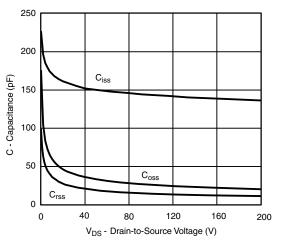
On-Resistance vs. Drain Current



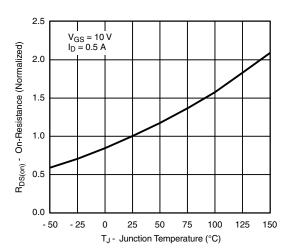
Gate Charge



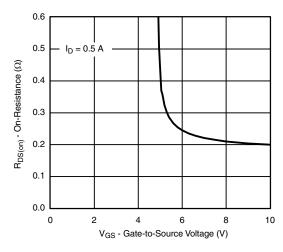
Source-Drain Diode Forward Voltage



Capacitance



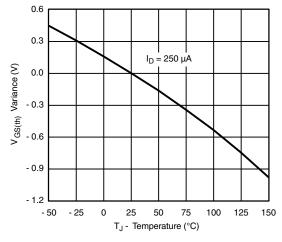
On-Resistance vs. Junction Temperature

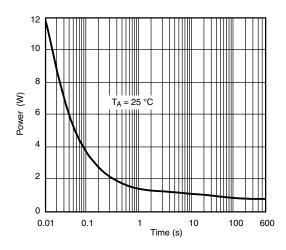


On-Resistance vs. Gate-to-Source Voltage



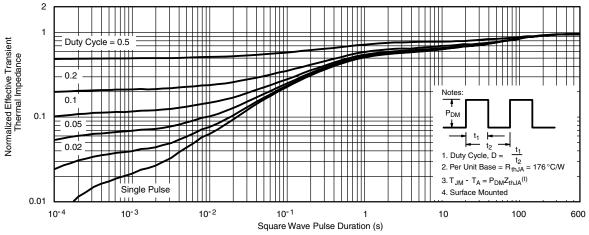
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Threshold Voltage

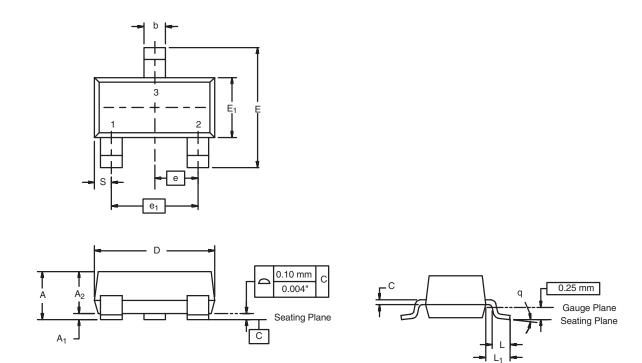
Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



SOT-23 (TO-236): 3-LEAD



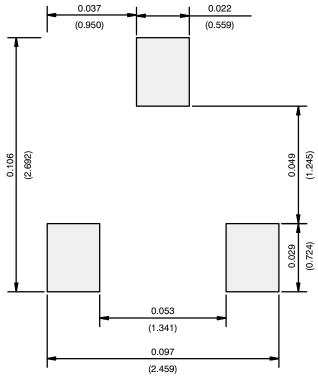
Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
Α	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
С	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
е	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.074	8 Ref
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025	Ref
S	0.50 Ref		0.020) Ref
q	3°	8°	3°	8°

DWG: 5479



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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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